

A METHOD OF PROCESSING A WAFER

ABSTRACT

According to embodiments of the present invention, a method of processing a wafer is
5 provided. The wafer includes a plurality of through-wafer interconnects extending from a
frontside surface of the wafer to a backside surface of the wafer. The method includes
removing a part of wafer material of the back-side such that a portion of the wafer
material between the through-wafer interconnects is removed, thereby exposing a portion
of the through-wafer interconnects, forming a layer of low-k dielectric material between
10 the through-wafer interconnects, and planarizing the layer of low-k dielectric material
such that a surface of the portion of the through-wafer interconnect is exposed.

Figure 2